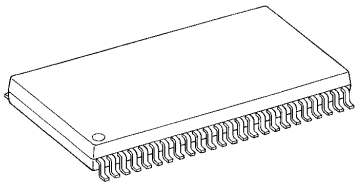
TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74LCX16374AFT

LOW-VOLTAGE 16-BIT D-TYPE FLIP-FLOP WITH 5V TOLERANT INPUTS AND OUTPUTS

The TC74LCX16374AFT is a high performance CMOS 16bit D-TYPE FLIP FLOP. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.
The device is designed for low-voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for both inputs and outputs.
This 16-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input ($\overline{OE}$) which are common to each byte. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. When the $\overline{OE}$ input is high, the outputs are in a high impedance state.
All inputs are equipped with protection circuits against static discharge.



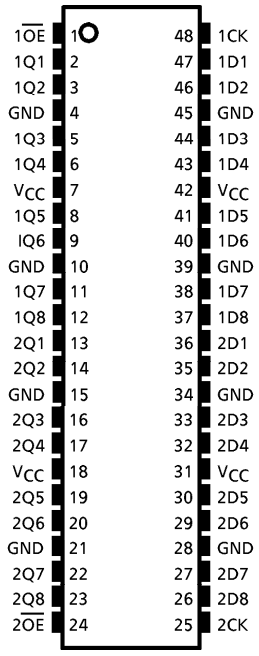
TSSOP48-P-0061-0.50

Weight : 0.25g (Typ.)

FEATURES

- Low Voltage Operation : $V_{CC} = 2.0 \sim 3.6V$
- High Speed Operation : $t_{pd} = 7.0ns$ (max.) at $V_{CC} = 3.0 \sim 3.6V$
- Output Current : $|I_{OH}| / I_{OL} = 24mA$ (min.) at $V_{CC} = 3.0V$
- Latch-up Performance : $\pm 500mA$
- Package : TSSOP
  (Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.

PIN CONNECTION



(TOP VIEW)

961001EBA2

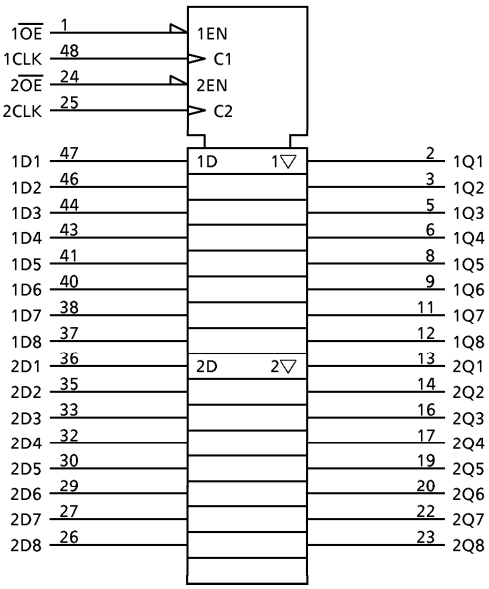
TRUTH TABLE

INPUT			OUTPUT
$1\overline{OE}$	1CK	1D1-1D8	1Q1-1Q8
H	X	X	Z
L	↓	X	Qn
L	↑	L	L
L	↑	H	H

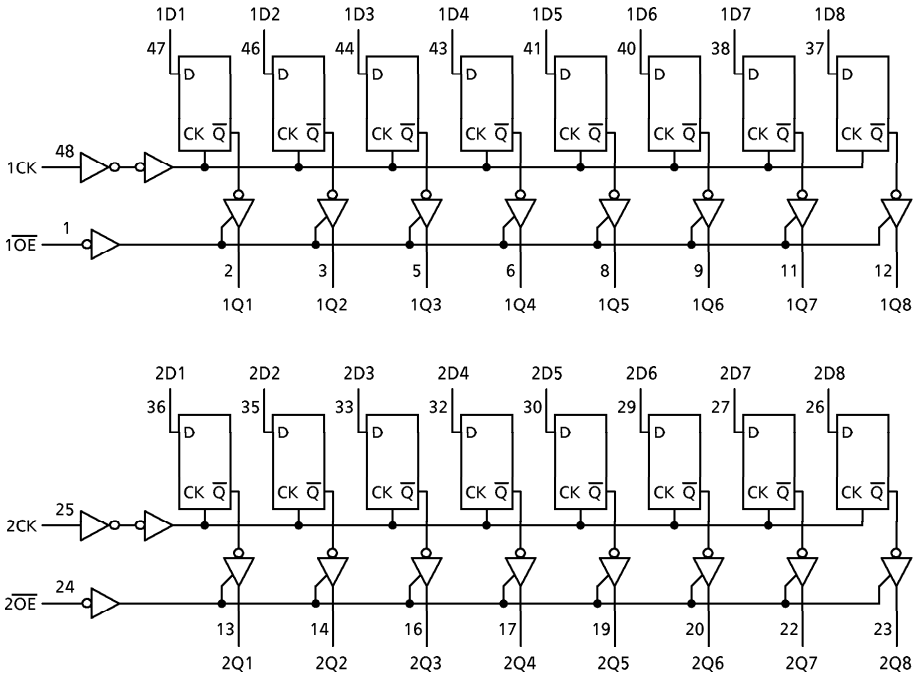
INPUT			OUTPUT
$2\overline{OE}$	2CK	2D1-2D8	2Q1-2Q8
H	X	X	Z
L	↓	X	Qn
L	↑	L	L
L	↑	H	H

X : Don't Care
Z : High impedance
Qn : No change

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



961001EBA2'

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	−0.5~7.0	V
Input Voltage	V_{IN}	−0.5~7.0	V
Output Voltage	V_{OUT}	−0.5~7.0 (Note 1)	V
		−0.5~V_{CC}+0.5 (Note 2)	
Input Diode Current	I_{IK}	−50	mA
Output Diode Current	I_{OK}	±50 (Note 3)	mA
DC Output Current	I_{OUT}	±50	mA
Power Dissipation	P_D	400	mW
DC V_{CC}/Ground Current Per Supply Pin	I_{CC}/I_{GND}	±100	mA
Storage Temperature	T_{stg}	−65~150	°C

(Note 1) Output in Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 3) $V_{OUT}<GND$, $V_{OUT}>V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~5.5 (Note 5)	V
		0~V_{CC} (Note 6)	
Output Current	I_{OH}/I_{OL}	±24 (Note 7)	mA
		±12 (Note 8)	
Operating Temperature	T_{opr}	−40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 9)	ns/V

(Note 4) Data Retention Only

(Note 5) Output in Off-State

(Note 6) High or Low State

(Note 7) V_{CC} = 3.0~3.6V

(Note 8) V_{CC} = 2.7~3.0V

(Note 9) V_{IN} = 0.8~2.0V, V_{CC} = 3.0V

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = −40~85°C)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V_{IH}			2.7~3.6	2.0	—	V
	"L" Level	V_{IL}			2.7~3.6	—	0.8	V
Output Voltage	"H" Level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100μA	2.7~3.6	V_{CC} −0.2	—	V
				I_{OH} = −12μA	2.7	2.2	—	
				I_{OH} = −18mA	3.0	2.4	—	
				I_{OH} = −24mA	3.0	2.2	—	
	"L" Level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100μA	2.7~3.6	—	0.2	V
				I_{OL} = 12mA	2.7	—	0.4	
				I_{OL} = 16mA	3.0	—	0.4	
				I_{OL} = 24mA	3.0	—	0.55	
Input Leakage Current		I_{IN}	V_{IN} = 0~5.5V		2.7~3.6	—	±5.0	μA
3-State Output Off-State Current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0~5.5V		2.7~3.6	—	±5.0	μA
Power Off Leakage Current		I_{OFF}	V_{IN} / V_{OUT} = 5.5V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		2.7~3.6	—	20.0	μA
			V_{IN} / V_{OUT} = 3.6~5.5V		2.7~3.6	—	±20.0	
Increase In I_{CC} Per Input		ΔI_{CC}	V_{IH} = V_{CC} − 0.6V		2.7~3.6	—	500	μA

AC characteristics (Ta = −40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	MIN.	MAX.	UNIT
Maximam Clock Frequency	f_{MAX}	(Fig.1, 2)	2.7	—	—	MHz
			3.3 ± 0.3	170	—	
Propagation Delay Time (CK - Q)	t_{pLH} t_{pHL}	(Fig.1, 2)	2.7	—	8.0	ns
			3.3 ± 0.3	1.5	7.0	
3-State Output Enable Time	t_{pZL} t_{pZH}	(Fig.1, 3)	2.7	—	8.2	ns
			3.3 ± 0.3	1.5	7.2	
3-State Output Disable Time	t_{pLZ} t_{pHZ}	(Fig.1, 3)	2.7	—	8.2	ns
			3.3 ± 0.3	1.5	7.2	
Minimum Pulse Width (CK)	t_w (H) t_w (L)	(Fig.1, 2)	2.7	4.0	—	ns
			3.3 ± 0.3	3.0	—	
Minimum Set-up Time	t_s	(Fig.1, 2)	2.7	2.5	—	ns
			3.3 ± 0.3	2.5	—	
Minimum Hold Time	t_h	(Fig.1, 2)	2.7	1.5	—	ns
			3.3 ± 0.3	1.5	—	
Output To Output Skew	t_{osLH} t_{osHL}	(Note 10)	2.7	—	—	ns
			3.3 ± 0.3	—	1.0	

(Note 10) Parameter guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic switching characteristics
(Ta = 25°C, Input $t_r = t_f = 2.5$ns, $C_L = 50$pF, $R_L = 500\Omega$)

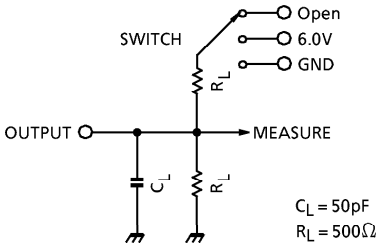
PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	V_{IH} = 3.3V, V_{IL} = 0V	3.3	0.8	V
Quiet Output Minimum Dynamic V_{OL}	$\|V_{OLV}\|$	V_{IH} = 3.3V, V_{IL} = 0V	3.3	0.8	V

Capacitive characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP	UNIT
Input Capacitance	C_{IN}	—	3.3	7	pF
Output Capacitance	C_{OUT}		3.3	8	pF
Power Dissipation Capacitance	C_{PD}	f_{IN} = 10MHz (Note 11)	3.3	25	pF

(Note 11) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation :
$I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16$. (Per bit)

Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0V
t_{pHZ}, t_{pZH}	GND
t_w, t_s, t_h, f_{MAX}	Open

AC WAVEFORM

Fig.2 t_{pLH}, t_{pHL}, t_w, t_s, t_h

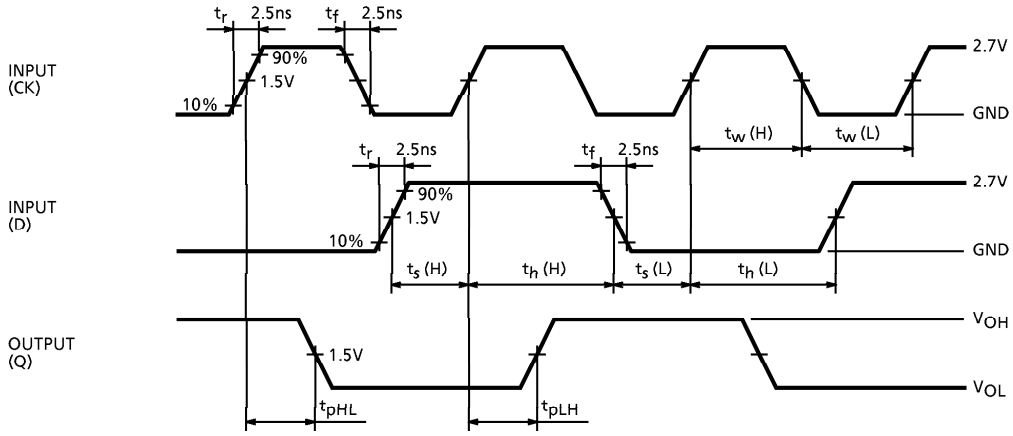
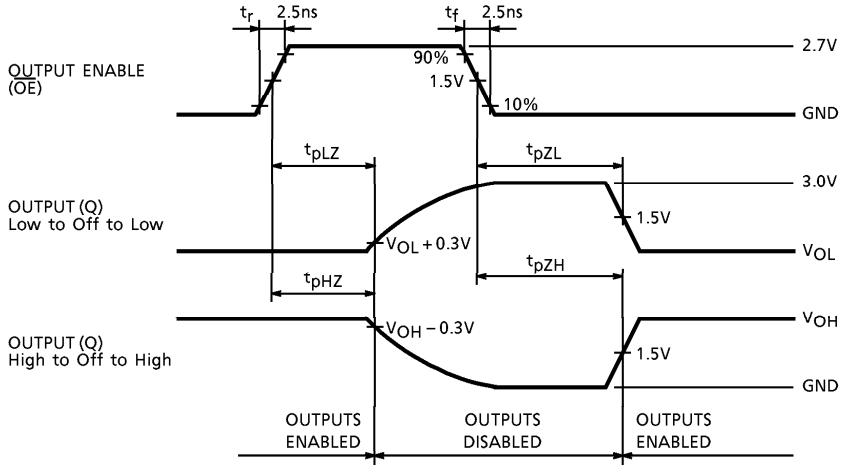
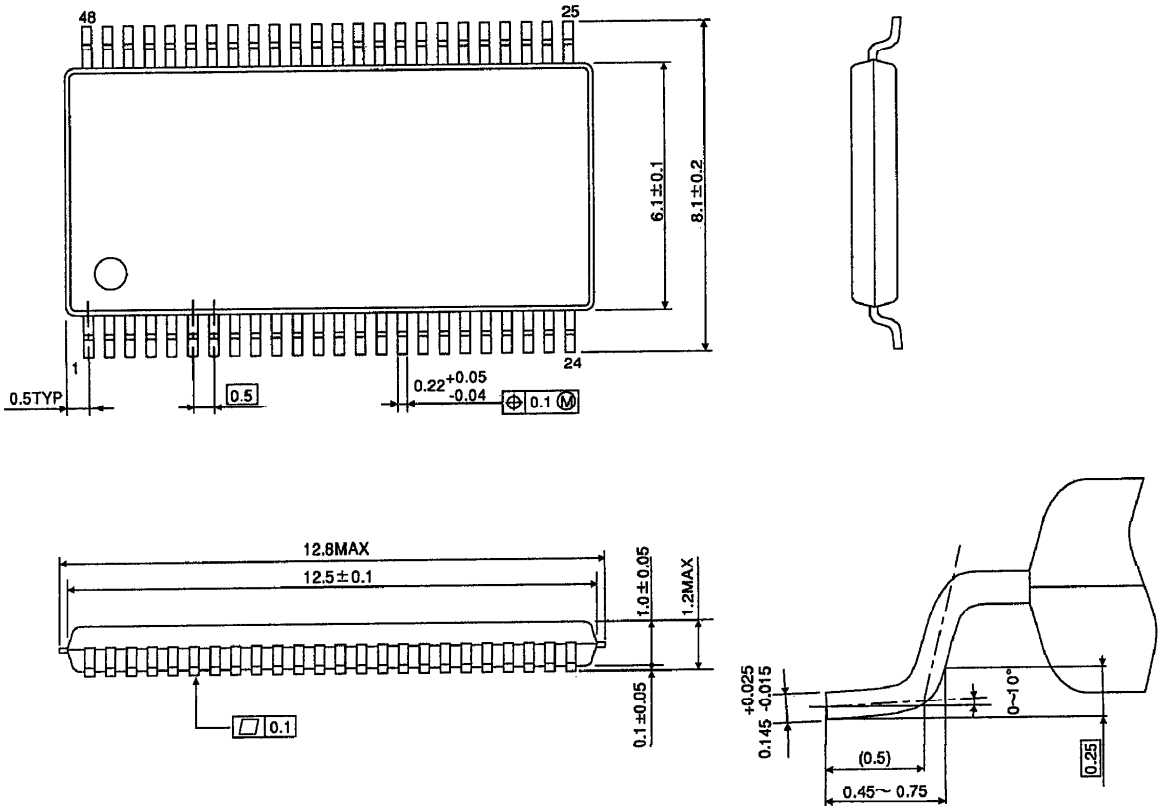


Fig.3 t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}



OUTLINE DRAWING

TSSOP48-P-0061-0.50 Unit : mm



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